

Far-infrared spectra of synthetic $^{[4]}[(\text{Al}_{2-x}\text{Ga}_x)(\text{Si}_{2-y}\text{Ge}_y)](\text{OH},\text{OD},\text{F})_2$ -kinoshitalite: Characterization and assignment of interlayer Ba-O_{inner} and Ba-O_{outer} stretching bands

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ABSTRACT

Far-infrared spectroscopy and X-ray diffraction Rietveld structure-refinement of synthetic kinoshitalite (Kn) solid solutions, $\text{BaMg}_3[(\text{Al}_{2-x}\text{Ga}_x)(\text{Si}_{2-y}\text{Ge}_y)]\text{O}_{10}(\text{OH},\text{OD},\text{F})_2$: ($x = 0.0\text{--}2.0$, $y = 0.0\text{--}2.0$), show that there is complete solid solution for all compositions in each (OH/OD)- and F-series: $^{[4]}[\text{Al}_2(\text{Si}_{2-y}\text{Ge}_y)]$ -, $^{[4]}[(\text{Al}_{2-x}\text{Ga}_x)\text{Si}_2]$ -, $^{[4]}[\text{Ga}_2(\text{Si}_{2-y}\text{Ge}_y)]$ -, $^{[4]}[(\text{Al}_{2-x}\text{Ga}_x)\text{Ge}_2]$ -Kn, and in OH/OD-for-F substituted $^{[4]}(\text{Al}_2\text{Si}_2)$ -, $^{[4]}(\text{Ga}_2\text{Si}_2)$ -, $^{[4]}(\text{Al}_2\text{Ge}_2)$ -, $^{[4]}(\text{Ga}_2\text{Ge}_2)$ -Kn end-member compositions. In the far-infrared region, 170–40 cm^{-1} , three kind of bands are observed; an in-plane tetrahedral torsional mode, an interlayer Ba-O_{inner} stretching vibration and a Ba-O_{outer} stretching vibration. With increasing tetrahedral $^{[4]}\text{Al}$ -for- $^{[4]}\text{Ga}$ and Si-for-Ge substitution, the frequencies and intensities of the tetrahedral in-plane torsional bands decrease in both the (OH/OD)- and F-bearing phases, but in the $^{[4]}(\text{Al}_2\text{Si}_2)$ -, $^{[4]}(\text{Ga}_2\text{Si}_2)$ -, $^{[4]}(\text{Al}_2\text{Ge}_2)$ -, $^{[4]}(\text{Ga}_2\text{Ge}_2)$ -Kn end-member compositions, the frequencies are unaffected by (OH/OD)-for-F substitution. The frequencies of both the Ba-O_{inner} and Ba-O_{outer} stretching bands increase with increasing $^{[4]}\text{Al}$ -for- $^{[4]}\text{Ga}$ and Si-for-Ge substitution, but the frequencies of the Ba-O_{inner} stretching bands decrease with increasing (OH/OD)-for-F substitution in the $^{[4]}(\text{Al}_2\text{Si}_2)$ -, $^{[4]}(\text{Ga}_2\text{Si}_2)$ -, $^{[4]}(\text{Al}_2\text{Ge}_2)$ -, $^{[4]}(\text{Ga}_2\text{Ge}_2)$ -Kn end-member compositions. The frequency difference between the Ba-O_{inner} and Ba-O_{outer} stretching bands is linearly related to the tetrahedral rotation angles (α), and these differences are about 10 cm^{-1} larger in the (OH/OD)-bearing phases than in the corresponding F-bearing phases. The ranges of absorption frequencies and their corresponding deformation modes are as follows: (1) in-plane tetrahedral torsional mode, 105–150 cm^{-1} ; (2) Ba-O_{inner} stretching vibration, 105–140 cm^{-1} ; and (3) Ba-O_{outer} stretching vibration, 75–90 cm^{-1} .

Keywords: Far-infrared spectra, synthetic kinoshitalite, in-plane torsional mode, Ba-O_{inner} stretching band, Ba-O_{outer} stretching band